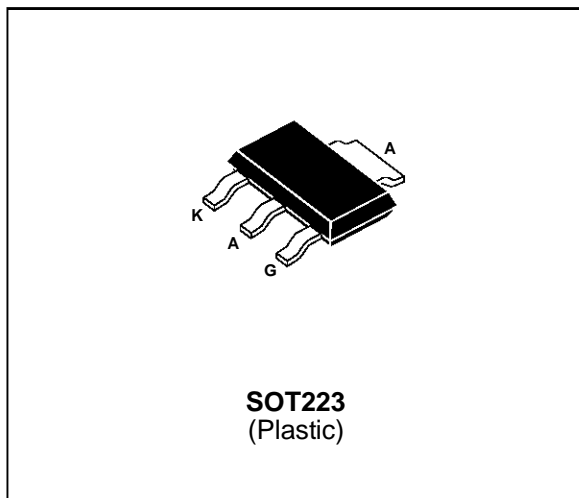


SENSITIVE GATE SCR
FEATURES

- $I_{T(RMS)} = 0.8A$
- $V_{DRM} = 100V$ to $400V$
- Low $I_{GT} < 200 \mu A$

DESCRIPTION

The P01xxxN series of SCRs uses a high performance planar PNP technology. These parts are intended for general purpose high volume applications using surface mount technology.


ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$ *	RMS on-state current (180° conduction angle)	$T_a = 70^\circ C$ 0.8	A
$I_{T(AV)}$ *	Mean on-state current (180° conduction angle)	$T_a = 70^\circ C$ 0.5	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	8
		$t_p = 10$ ms	7
I_t^2	I_t^2 Value for fusing	$t_p = 10$ ms	0.24 A^2s
di/dt	Critical rate of rise of on-state current $I_G = 10$ mA $di_G/dt = 0.1$ A/ μs .	30	A/ μs
T_{stg} T_j	Storage and operating junction temperature range	- 40, + 150 - 40, + 125	$^\circ C$
TI	Maximum lead temperature for soldering during 10s	260	$^\circ C$

* : With $5cm^2$ copper ($e=35\mu m$) surface under tab.

Symbol	Parameter	Voltage				Unit
		A	B	C	D	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$ $R_{GK} = 1K\Omega$	100	200	300	400	V

P01xxxN

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient *	60	°C/W
Rth(j-t)	Junction to tab for DC	30	°C/W

* : With 5cm² copper (e=35μm) surface under tab.

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 0.1 \text{ W}$ $P_{GM} = 2 \text{ W}$ ($t_p = 20 \mu\text{s}$) $I_{GM} = 1 \text{ A}$ ($t_p = 20 \mu\text{s}$)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions				Sensitivity			Unit
					02	09	11	
I _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MIN	-	-	4	μA	
			MAX	200	1	25		
V _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MAX	0.8			V	
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ R _{GK} = 1 KΩ	T _j = 125°C	MIN	0.1			V	
V _{RGM}	I _{RG} = 10μA	T _j = 25°C	MIN	8			V	
t _{gd}	V _D =V _{DRM} I _{TM} = 3 x I _{T(AV)} dI _G /dt = 0.1A/μs I _G = 10mA	T _j = 25°C	TYP	0.5			μs	
I _H	I _T = 50mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	5			mA	
I _L	I _G =1mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	6			mA	
V _{TM}	I _{TM} = 1.6A t _p = 380μs	T _j = 25°C	MAX	1.95			V	
I _{DRM} I _{RRM}	V _D = V _{DRM} R _{GK} = 1 KΩ V _R = V _{RRM}	T _j = 25°C	MAX	1			μA	
		T _j = 125°C	MAX	100			μA	
dV/dt	V _D =67%V _{DRM} R _{GK} = 1 KΩ	T _j = 125°C	MIN	25	25	50	V/μs	
t _q	I _{TM} = 3 x I _{T(AV)} V _R =35V dI/dt=10A/μs t _p =100μs dV/dt=10V/μs V _D = 67%V _{DRM} R _{GK} = 1 KΩ	T _j = 125°C	MAX	200			μs	

ORDERING INFORMATION

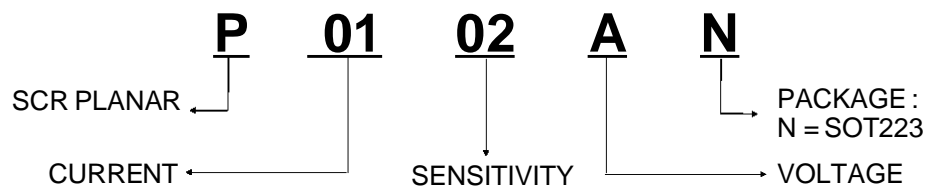


Fig.1 : Maximum average power dissipation versus average on-state current.

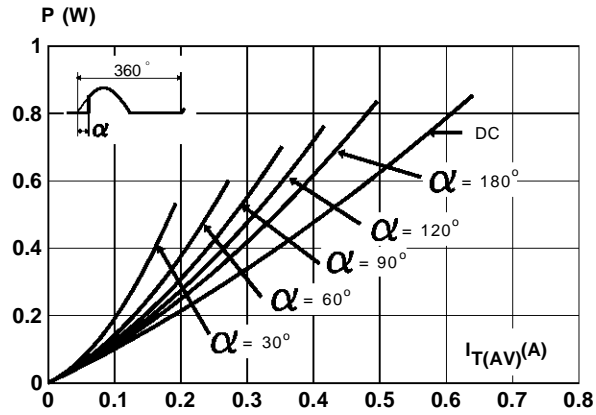


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Ttab).

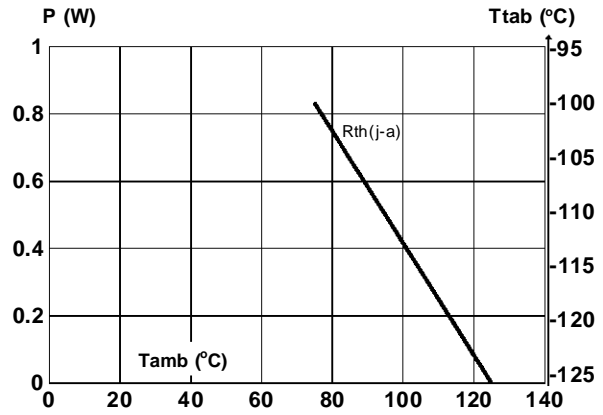


Fig.3 : Average on-state current versus tab temperature.

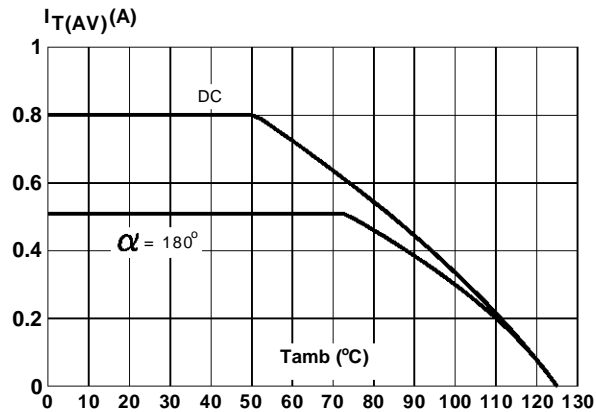


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

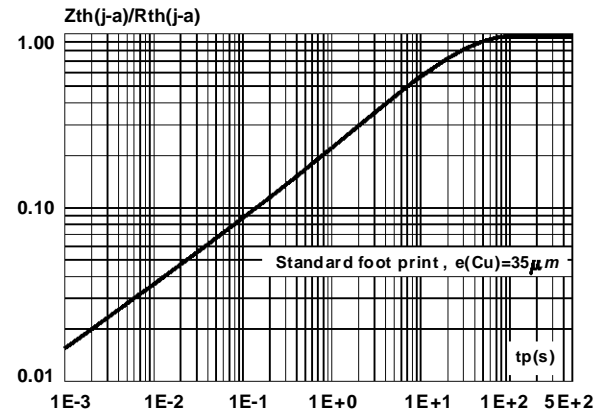


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

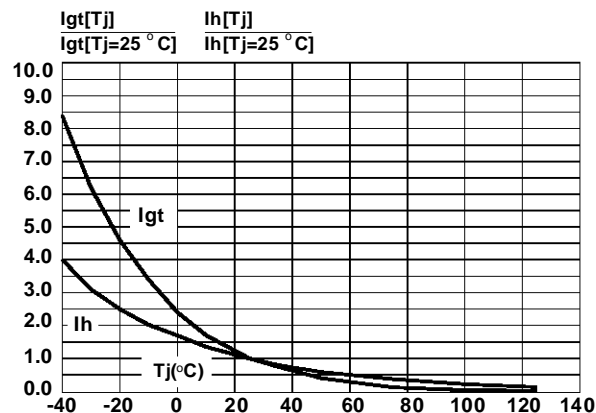


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

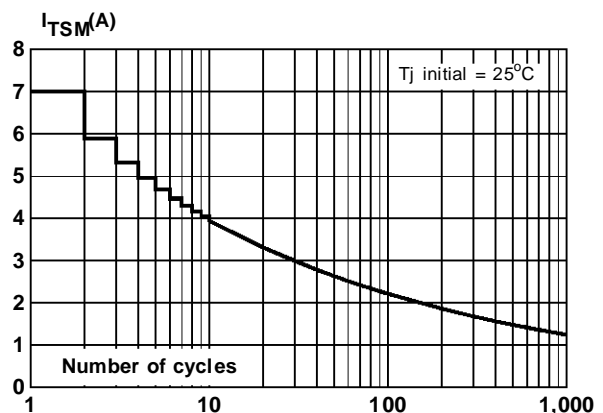


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

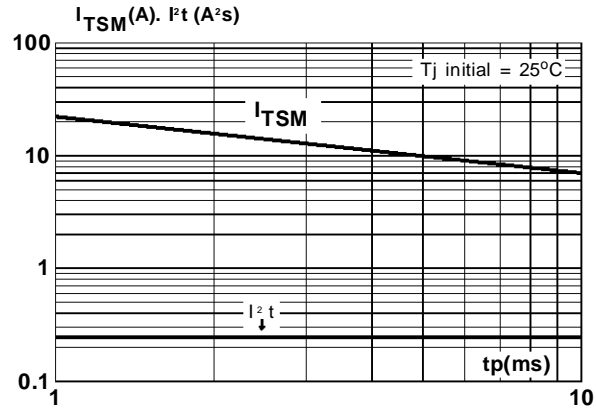


Fig.8 : On-state characteristics (maximum values).

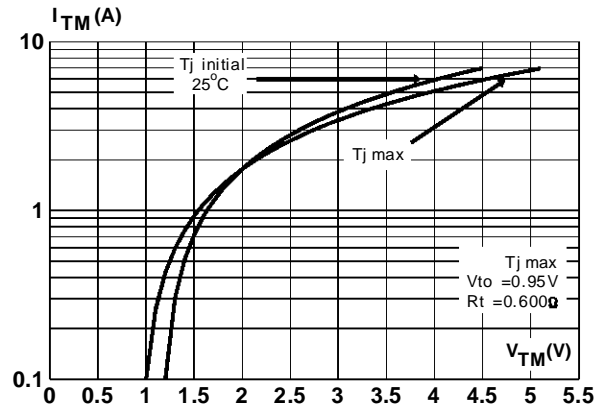
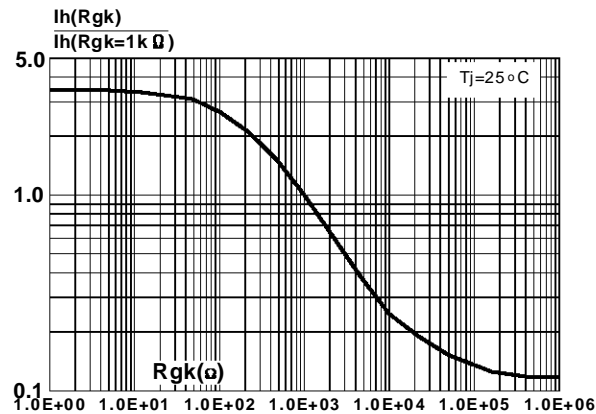
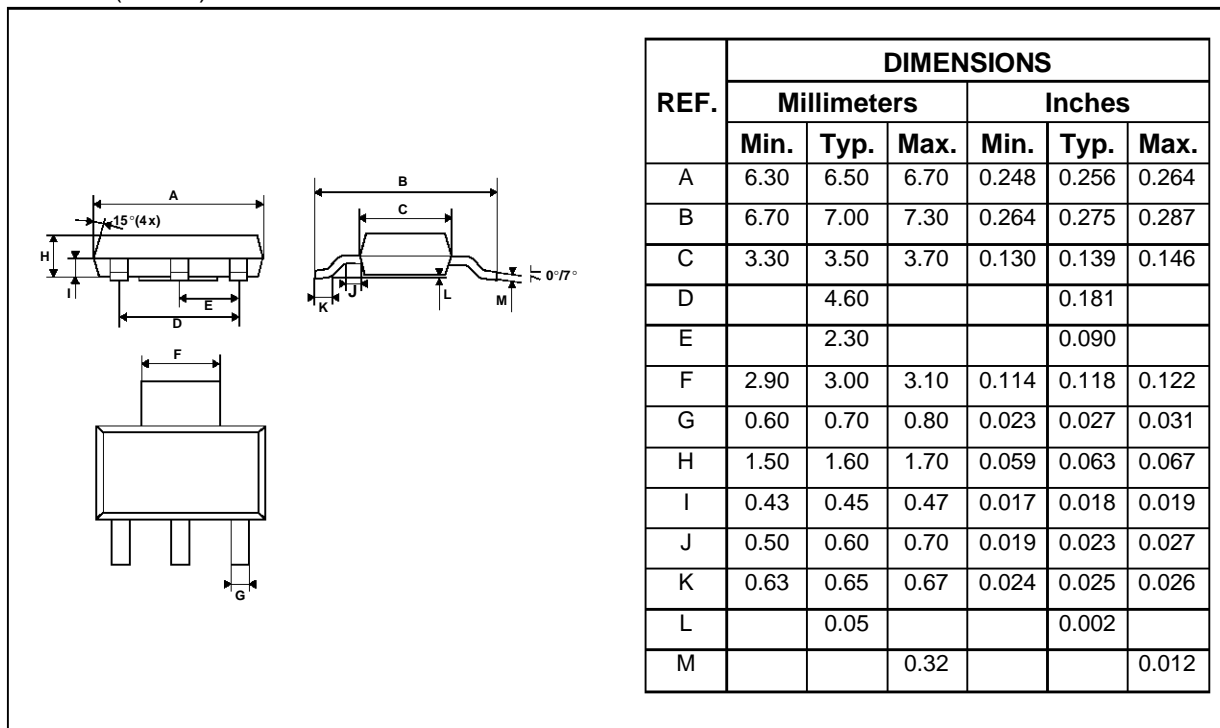


Fig.9 : Relative variation of holding current versus gate-cathode resistance (typical values).

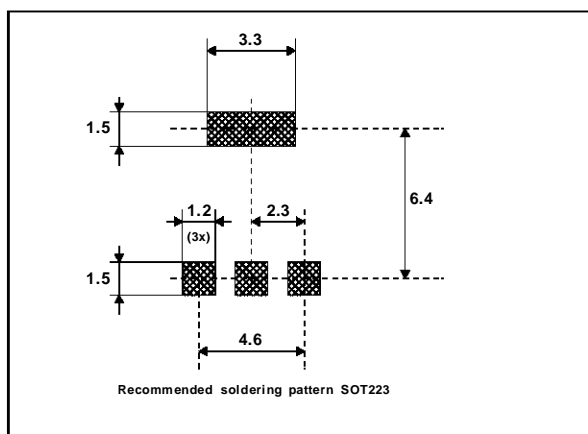


PACKAGE MECHANICAL DATA
SOT223 (Plastic)



Weight : 0.11g

FOOT PRINT



MARKING

Type	Marking
P0102AN	P2A
P0102BN	P2B
P0102CN	P2C
P0102DN	P2D
P0111AN	P1A
P0111BN	P1B
P0111CN	P1C
P0111DN	P1D
P0109AN	P9A
P0109BN	P9B
P0109CN	P9C
P0109DN	P9D

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